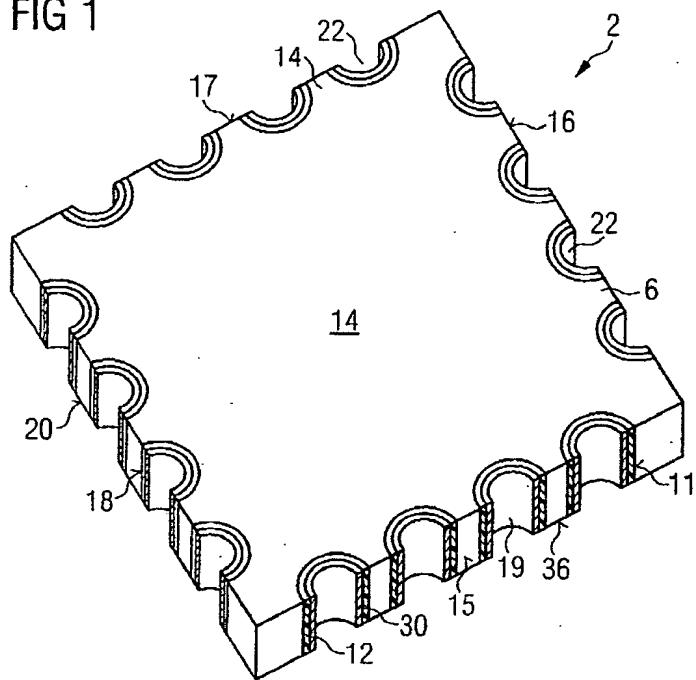


Docket No. I431.103.101/FIN 423 US  
**ELECTRONIC COMPONENT AND SEMICONDUCTOR  
WAFER, AND METHOD FOR PRODUCING THE SAME**

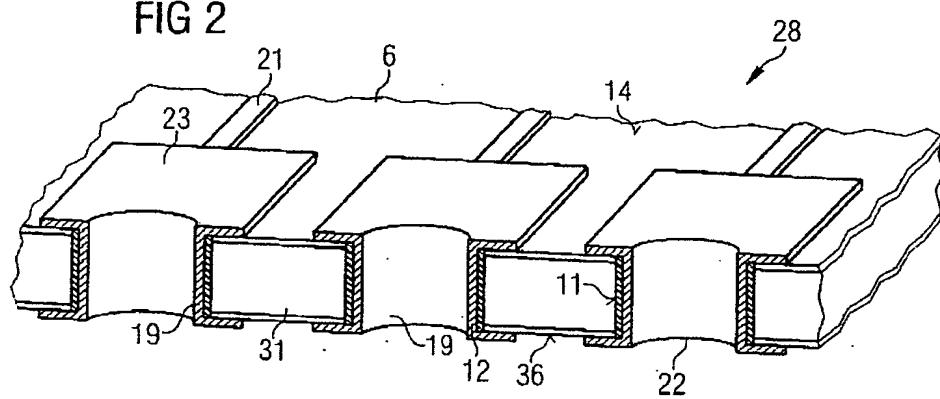
Michael Bauer et al.

1/7

**FIG 1**



**FIG 2**



Docket No. I431.103.101/FIN 423 US  
**ELECTRONIC COMPONENT AND SEMICONDUCTOR  
WAFER, AND METHOD FOR PRODUCING THE SAME**  
Michael Bauer et al.  
2/7

FIG 3

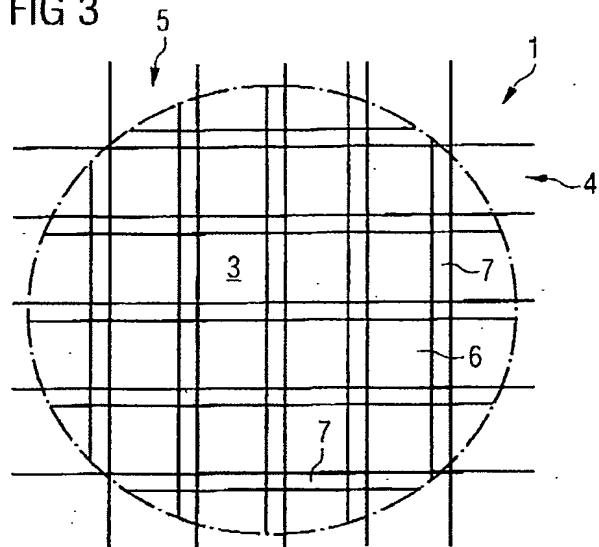
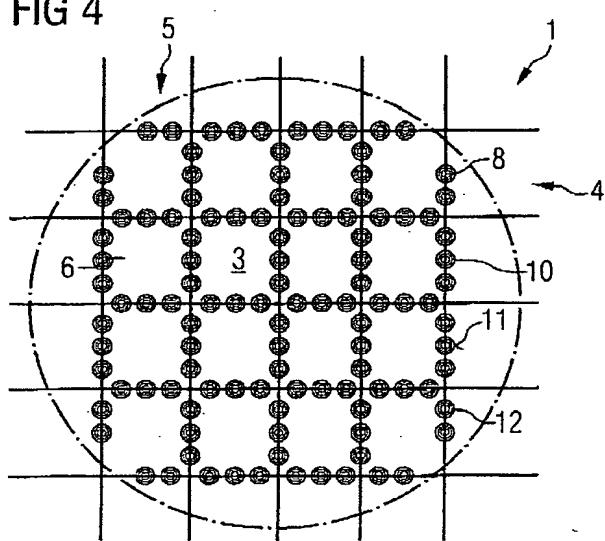


FIG 4



Docket No. I431.103.101/FIN 423 US  
**ELECTRONIC COMPONENT AND SEMICONDUCTOR  
WAFER, AND METHOD FOR PRODUCING THE SAME**  
Michael Bauer et al.

3/7

FIG 5

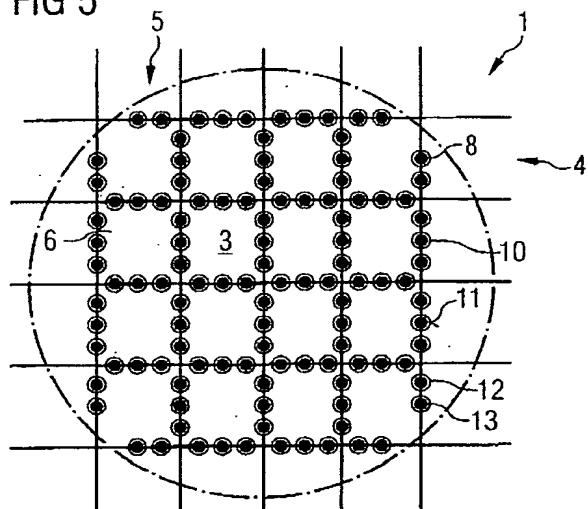
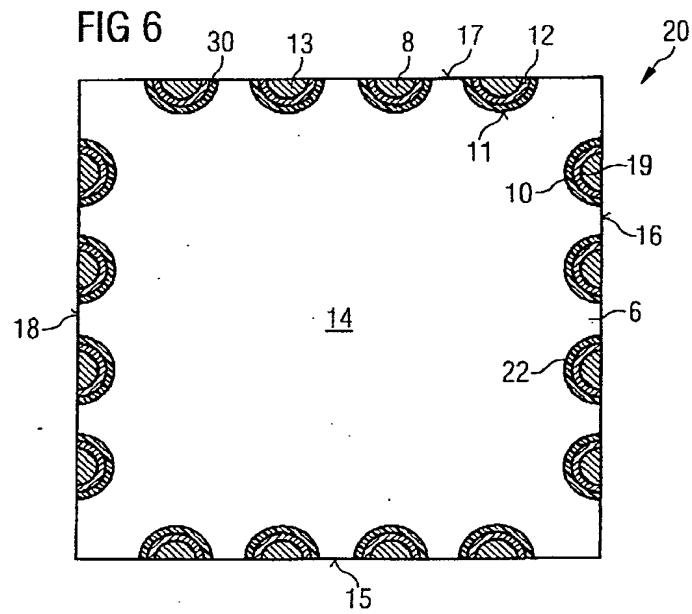
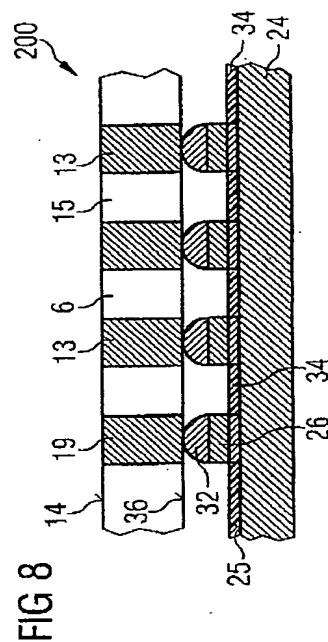
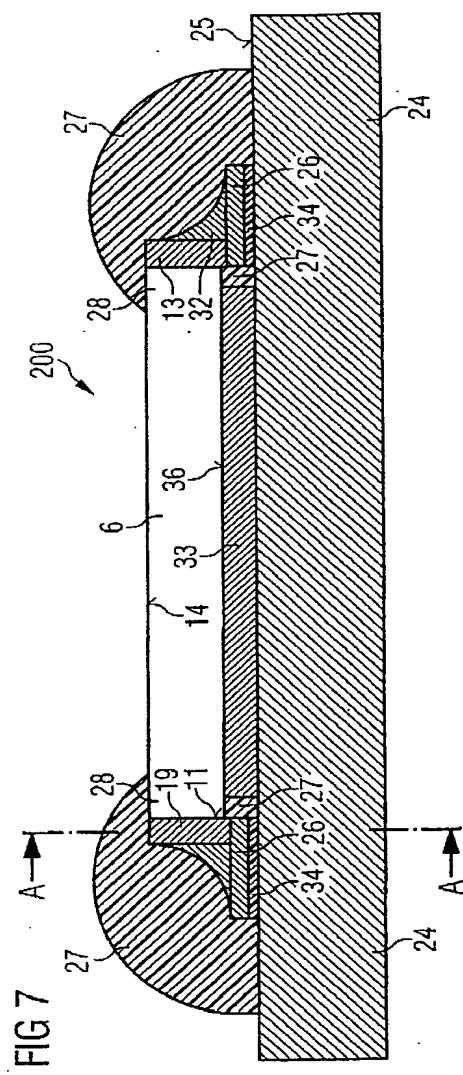


FIG 6



Docket No. I431.103.101/FIN 423 US  
**ELECTRONIC COMPONENT AND SEMICONDUCTOR  
WAFER, AND METHOD FOR PRODUCING THE SAME**  
Michael Bauer et al.

4/7



Docket No. I431.103.101/FIN 423 US  
**ELECTRONIC COMPONENT AND SEMICONDUCTOR  
WAFER, AND METHOD FOR PRODUCING THE SAME**

Michael Bauer et al.

5/7

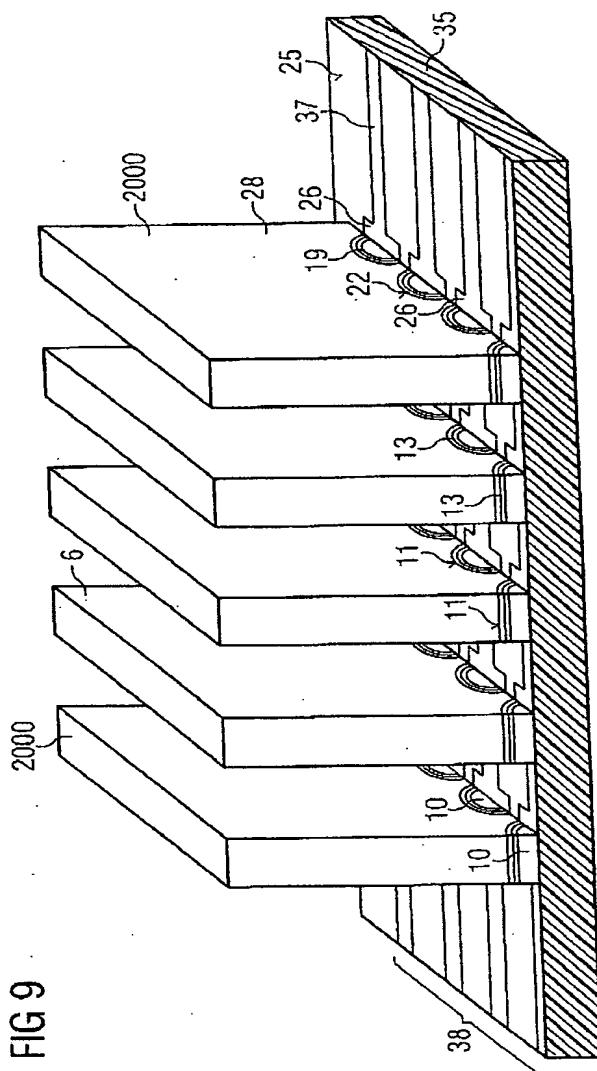


FIG 9

Docket No. I431.103.101/FIN 423 US  
**ELECTRONIC COMPONENT AND SEMICONDUCTOR  
WAFER, AND METHOD FOR PRODUCING THE SAME**  
Michael Bauer et al.  
6/7

FIG 10

